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## (54) FORMATION OF RESIST PATTERN

### (57)Abstract:

PURPOSE: To prevent charge up by using a conductive film of poly $\beta$ -diketone as a flattening layer.

CONSTITUTION: The poly $\beta$ -diketone layer is formed as the flattening layer on a semiconductor substrate, for example, Al/Si substrate in formation of a resist pattern for which multi-layered resist layers having conductive films are used under a resist layer. After the resist layer is then formed, the layer is patterned. Since the poly $\beta$ -diketone has conductivity, the charge stagnating in the resist on the poly $\beta$ -diketone layer flows through the poly $\beta$ -diketone to the semiconductor substrate. The charge up is thereby prevented.

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